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1-6 (Cancelled).

1-7 (Previously Presented) A process for polishing wafers comprising:
mixing a marker with a slurry to form a slurry mixture;
performing chemical mechanical polishing on a wafer using said slurry mixture;
rinsing said slurry mixture from said wafer; and
checking said wafer for marker residue,
wherein said checking comprises residual gas analysis and said marker has a higher vapor pressure than said slurry.

2-8 (Previously Presented) A process for polishing and cleaning silicon wafers comprising:
mixing a marker with a slurry to form a slurry mixture, wherein said marker has a higher vapor pressure than said slurry;
performing chemical mechanical polishing on a silicon wafer using said slurry mixture;
rinsing said slurry mixture from said silicon wafer; and
checking said silicon wafer for marker residue.

3-9 (Original) The process in claim 8, wherein said checking comprises illuminating said silicon wafer with a light source and detecting a spectrum of light returned from said silicon wafer.

4-10 (Original) The process in claim 9, wherein said checking illuminates light to, and detects light from, edges of said silicon wafer.

5-11 (Original) The process in claim 9, wherein said light source comprises one of a light emitting diode and a laser.

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12- (Original) The process in claim 9, wherein said marker has a characteristic phosphorescence upon illumination by said light source.

13- (Original) The process in claim 8, wherein said marker is mixed with said slurry in small enough quantities so as to not affect a polishing capability of said slurry.

14. (Previously Presented) A process for polishing and cleaning silicon wafers comprising:
mixing a marker with a slurry to form a slurry mixture;
performing chemical mechanical polishing on a silicon wafer using said slurry mixture;
rinsing said slurry mixture from said silicon wafer;
checking said silicon wafer for marker residue; and
repeating said rinsing process if said checking process detects said marker residue on said wafer,
wherein said checking comprises reactive gas analysis and said marker has a higher vapor pressure than said slurry.

15-20. (Canceled).